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# **STD826**

### PNP MEDIUM POWER TRANSISTOR

### Features

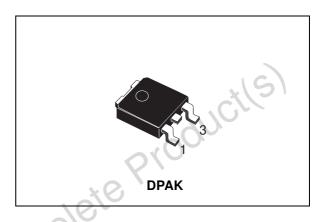
- SURFACE MOUNTING DEVICE IN MEDIUM POWER DPAK PACKAGE
- AVAILABLE IN TAPE & REEL PACKING
- IN COMPLIANCE WITH THE 2002/93/EC EUROPEAN DIRECTIVE

### Applications

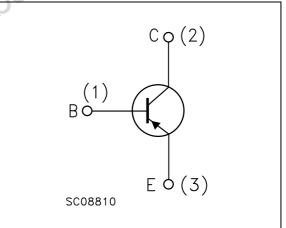
- VOLTAGE REGULATION
- RELAY DRIVER
- GENERIC SWITCH

### Description

The STD826 is PNP transistor manufactured using planar Technology resulting in rugged high performance devices.



### Internal Schematic Diagram



# Order codes

Part Number	Marking	Package	Packing	
STD826T4	D826	DPAK	Tape & reel	

### **Absolute Maximum Ratings** 1

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage $(I_E = 0)$	-60	V
V <sub>CEO</sub>	Collector-Emitter Voltage $(I_B = 0)$	-30	V
$V_{\text{EBO}}$	Collector-Base Voltage $(I_C = 0)$	-5	V
Ι <sub>C</sub>	Collector Current	-3	Α
I <sub>CM</sub>	Collector Peak Current (t <sub>P</sub> < 5ms)	-6	Α
Ι <sub>Β</sub>	Base Current	-1	Α
I <sub>BM</sub>	Base Peak Current (t <sub>P</sub> < 5ms)	-2	Α
P <sub>TOT</sub>	Total dissipation at $T_c = 25^{\circ}C$	15	W
T <sub>STG</sub>	Storage Temperature	-65 to 150	°C
Τ <sub>J</sub>	Max. Operating Junction Temperature	150	°C
fable 2.	Thermal Data	3	

#### Table 1. **Absolute Maximum Rating**

#### Table 2. **Thermal Data**

Symbol	Parameter	SOIL SOIL	Valu	e Unit
R <sub>thJ-case</sub>	Thermal Resistance Junction-Case	М	ax 8.33	3 °C/W
00501	ete Product(S)			
0,02				

2/10



## 2 Electrical Characteristics

Symbol	Parameter	Test Condit	ions	Min.	Тур.	Max.	Unit
I <sub>CES</sub>	Collector Cut-off Current (V <sub>BE</sub> = 0)	V <sub>CE</sub> = -60V				-10	μΑ
I <sub>CEO</sub>	Collector Cut-off Current $(I_B = 0)$	V <sub>CE</sub> = -30V				-100	μA
I <sub>EBO</sub>	Emitter Cut-off Current $(I_{C} = 0)$	V <sub>EB</sub> = -5V				-10	μA
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage (I <sub>E</sub> = 0)	I <sub>C</sub> = -100μA		-60	21	Cill	v
V <sub>(BR)CEO</sub> Note: 1	Collector-Emitter Breakdown Voltage ( $I_B = 0$ )	I <sub>C</sub> = -10 mA		-30	20,		V
V <sub>(BR)EBO</sub>	Collector-Emitter Breakdown Voltage (I <sub>C</sub> = 0)	I <sub>E</sub> = -100 μA		-5			V
V <sub>CE(sat)</sub> Note: 1	Collector-Emitter Saturation Voltage		I <sub>B</sub> = -50 mA I <sub>B</sub> = -100 mA I <sub>B</sub> = -150 mA			-0.4 -0.7 -1.1	V V V
V <sub>BE(sat)</sub> Note: 1	Base-Emitter Saturation Voltage	I <sub>C</sub> = -2 A	l <sub>B</sub> = -100 mA			-1.2	V
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = -100 mA I <sub>C</sub> = -1 A I <sub>C</sub> = -3 A	V <sub>CE</sub> = -2 V V <sub>CE</sub> = -2 V V <sub>CE</sub> = -2 V	100 80 30		300	
f <sub>T</sub>	Transistor Frequency	V <sub>CE</sub> = -10 V	I <sub>c</sub> = - 0.1 A		100		MHz

Table 3.Electrical Characteristics ( $T_{CASE} = 25^{\circ}C$ ; unless otherwise specified)

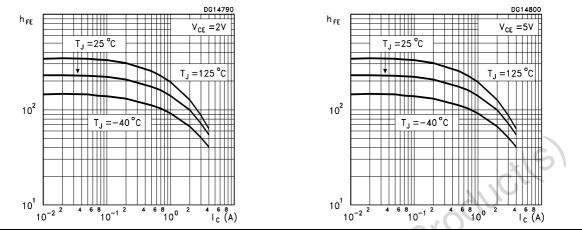
Note: 1 Pulsed duration = 300  $\mu$ s, duty cycle  $\leq$ 1.5%.

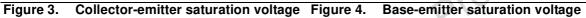


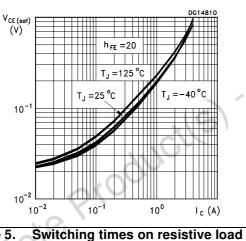
#### **Electrical characteristics (curve)** 2.1

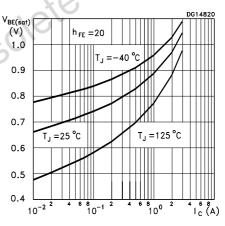
#### Figure 1. **DC Current Gain**

Figure 2. **DC Current Gain** 

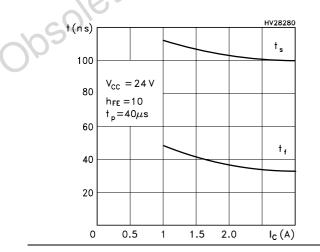


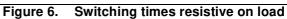


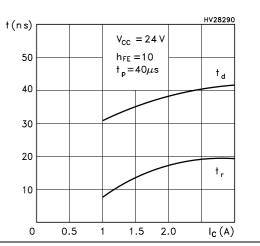






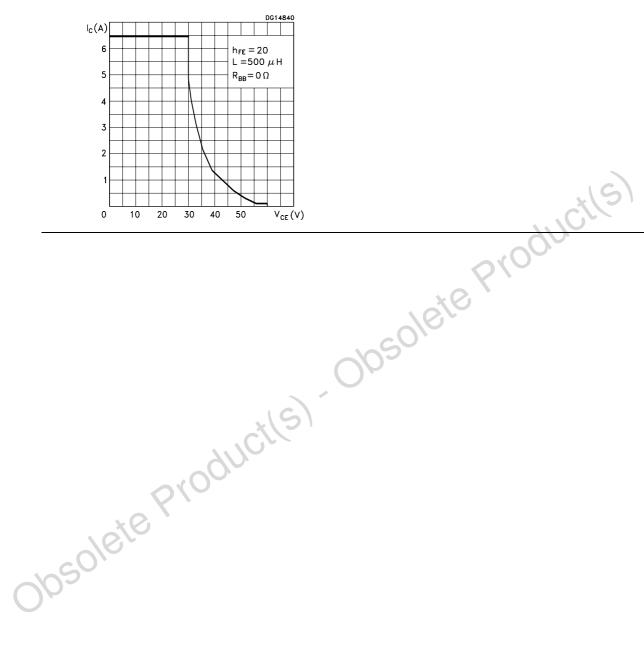








### Figure 7. Reverse biased area





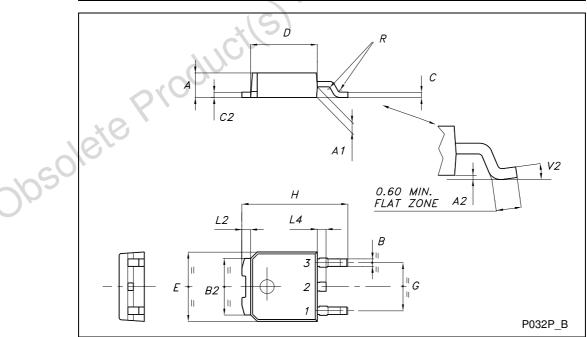
### 3 Package Mechanical Data

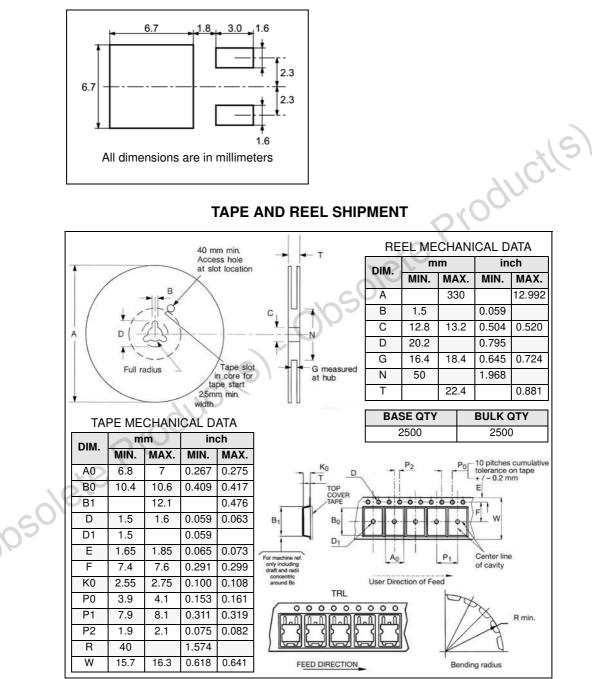
In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com Obsolete Product(s)-Obsolete Product(s)



DIM.	mm			inch		
2	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
В	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.213
С	0.45		0.60	0.018		0.024
C2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.236	010	0.244
E	6.40		6.60	0.252		0.260
G	4.40		4.60	0.173		0.181
Н	9.35		10.10	0.368		0.398
L2		0.8			0.031	
L4	0.60		1.00	0.024		0.039
V2	0°		8°	0°		0°

### **TO-252 (DPAK) MECHANICAL DATA**





**DPAK FOOTPRINT** 





### 4 Revision History

Date	Revision	Changes
03-Aug-2005	1	Initial release.

obsolete Product(s) - Obsolete Product(s)



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